19-4591; Rev 0; 4/09

EVALUATION KIT AVAILABLE

high-voltage supply inputs.

# 

### Dual/Quad, Unipolar/Bipolar, **High-Voltage Digital Pulsers**

#### **General Description**

Applications

The MAX4940/MAX4940A integrated circuits generate

high-voltage, high-frequency, unipolar or bipolar pulses

from low-voltage logic inputs. These guad/dual pulsers

feature independent logic inputs, independent high-volt-

age pulser outputs with active clamps and independent

The MAX4940/MAX4940A feature quad, high-voltage puls-

ers with  $8.5\Omega$  output impedance for the high-voltage

outputs and a  $21\Omega$  impedance for the active clamp. The high-voltage outputs can provide 2.0A (typ) output current.

All devices use two logic inputs per channel to control the positive and negative pulses. The MAX4940/

MAX4940A have a dedicated input to control the active

clamp. All devices feature an independent enable input

EN. All digital inputs are CMOS compatible (see the

The MAX4940/MAX4940A are available in a 56-pin, 8mm x

8mm, TQFN exposed pad package and are specified over

the 0°C to +70°C commercial temperature range. Warning: Exercise caution. The MAX4940/MAX4940A are

Ordering Information/Selector Guide).

designed to operate with high voltages.

Flaw Detection **Piezoelectric Drivers** 

**Test Instruments** 

Cleaning Equipment

Ultrasound Medical Imaging

**Features** 

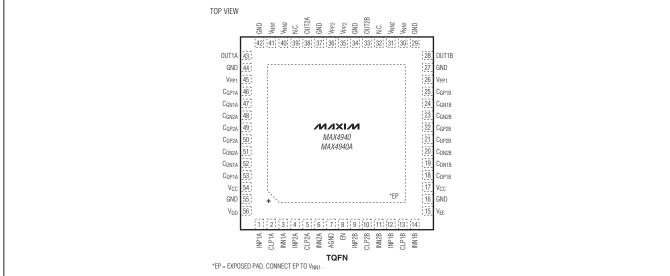
- High-Density Quad-Channel Pulser in One Package
- ♦ 0 to +220V Unipolar or ±110V Bipolar Outputs
- 8.5Ω (typ) Output Impedance and 2.0A (typ) **Output Current**
- 21Ω (typ) Always-On Active Clamp with Integrated **Blocking Diodes**
- Integrated Output Diodes (MAX4940A Only)
- No Special Power-Supply Sequencing Required for Trilevel Applications
- Matched Rise/Fall Times and Matched **Propagation Delays**
- CMOS-Compatible Logic Inputs
- 56-Pin, 8mm x 8mm, TQFN Package

#### **Ordering Information/ Selector Guide**

PART	OUTPUT BLOCKING DIODE	OUTPUT CURRENT (A)	PIN- PACKAGE
MAX4940CTN+	None	2.0 (typ)	56 TQFN-EP*
MAX4940ACTN+	OUT2A, OUT2B	2.0 (typ)	56 TQFN-EP*

Note: Devices operate over the 0°C to +70°C temperature range. +Denotes a lead(Pb)-free/RoHS-compliant package. \*EP = Exposed pad.

#### Pin Configuration



#### 

Maxim Integrated Products 1

**|AX4940/MAX4940**A

For pricing, delivery, and ordering information, please contact Maxim Direct at 1-888-629-4642, or visit Maxim's website at www.maxim-ic.com.

#### **ABSOLUTE MAXIMUM RATINGS**

(Voltages referenced to GND.)

(	
V <sub>DD</sub> Logic Supply Voltage0.3V to +6V	
V <sub>CC</sub> Output Driver Positive Supply Voltage0.3V to +15V	
VEE Output Driver Negative Supply Voltage15V to +0.3V	
VPP_ High-Positive Supply Voltage0.3V to (V <sub>NN_</sub> + 220V)	
V <sub>NN</sub> _Low-Negative Supply Voltage220V to +0.3V	
VPP1 - VNN1, VPP2 - VNN2 Supply Voltage0.6V to +250V	
INP_, INN_, CLP_, EN Logic Input0.3V to (V <sub>DD</sub> + 0.3V)	
$C_{GN}$ Voltage (-0.3V + $V_{NN}$ ) to (+15V + $V_{NN}$ )	
C <sub>GP</sub> _Voltage(+0.3V + V <sub>PP</sub> ) to (-15V + V <sub>PP</sub> )	

CDP_, CDN_ Voltage Continuous Power Dissipation ( $T_A = +70^{\circ}C$ )	0.3V to VCC
56-Pin TQFN (derate 47.6mW/°C above +70°C	C)3809mW
Thermal Resistance (Note 1)	
θJA	21°C/W
θJC	1°C/W
Operating Temperature Range	0°C to +70°C
Junction Temperature	+150°C
Storage Temperature Range6	5°C to +150°C
Lead Temperature (soldering, 10s)	+300°C

Note 1: Package thermal resistances were obtained using the method described in JEDEC specification JESD51-7, using a fourlayer board. For detailed information on package thermal considerations, refer to <u>www.maxim-ic.com/thermal-tutorial</u>.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

#### ELECTRICAL CHARACTERISTICS

 $(V_{DD} = +3V, V_{CC} = +12V, V_{EE} = -12V, V_{PP} = +100V, V_{NN} = -100V, T_A = T_{MIN}$  to T<sub>MAX</sub>, unless otherwise noted. Typical values are at T<sub>A</sub> = +25°C.) (Note 2)

PARAMETER	SYMBOL	CONDITIONS	MIN	TYP	MAX	UNITS
POWER SUPPLY (VDD, VCC, VE	E, VPP_, VNN	_)				
Logic Supply Voltage	VDD		2.37	3	6	V
Positive Drive Supply Voltage	Vcc		4.75	12	12.6	V
Negative Drive Supply Voltage	VEE		1.05 x (-V <sub>CC</sub> )	-VCC	0.95 x (-V <sub>CC</sub> )	V
High-Side Supply Voltage	VPP1		0		+200	V
Low-Side Supply Voltage	VNN1		-200		0	V
High-Side Supply Voltage	VPP2		0		VPP1	V
Low-Side Supply Voltage	VNN2		VNN1		0	V
VPP V <sub>NN</sub> _ Supply Voltage			0		+200	V
SUPPLY CURRENT (for single of	hannel)					
		$V_{INN}_{VINP}_{VCLP} = 0 \text{ or } V_{DD}, V_{EN} = 0$			1	μA
V <sub>DD</sub> Supply Current	IDD	$V_{EN} = V_{DD}$ , $V_{CLP} = 0$ or $V_{DD}$ , $V_{INN} = V_{INP}$ , f = 5MHz, one channel switching		100	200	μA
		V <sub>EN</sub> = 0 (static)			1	
		V <sub>EN</sub> = V <sub>DD</sub> (static)		10		μA
V <sub>CC</sub> Supply Current	ICC_	$V_{EN} = V_{DD}, V_{CLP} = 0 \text{ or } V_{DD}, V_{INN} = V_{INP}, f = 5MHz, V_{CC} = +12V, V_{DD} = +3V,$ one channel switching	36			- mA
		$\label{eq:VEN} \begin{array}{l} V_{EN} = V_{DD},  V_{CLP\_} = 0 \mbox{ or } V_{DD},  V_{INN\_} = \\ V_{INP\_},  f = 5 \mbox{MHz},  V_{CC} = +5 \mbox{V},  V_{DD} = +3 \mbox{V}, \\ \mbox{ one channel switching} \end{array}$		15		

#### **ELECTRICAL CHARACTERISTICS (continued)**

 $(V_{DD} = +3V, V_{CC} = +12V, V_{EE} = -12V, V_{PP} = +100V, V_{NN} = -100V, T_A = T_{MIN}$  to T\_MAX, unless otherwise noted. Typical values are at T\_A = +25°C.) (Note 2)

PARAMETER	SYMBOL	CO	ONDITIONS	MIN	TYP	MAX	UNITS	
		VEN = 0 or VDD (	static)			1		
VEE_ Supply Current	IEE_		VDD, VCLP_ = VDD, 5MHz, four pulses, nnel switching			100	μA	
			= V <sub>DD</sub> , V <sub>CLP</sub> _ = V <sub>DD</sub> , 5MHz, four pulses, nnel switching			200		
		VEN = 0 or VDD (	static)			1	μΑ	
Voo Supply Current			$P_{-} = 0 \text{ or } V_{DD}, V_{INN_{-}} = V_{PP_{-}} = +5V, V_{NN_{-}} = -5V,$ nnel switching		9			
VPP_ Supply Current	IPP_	VEN = VDD, VCLF VPP_ = +80V, VN f = 10MHz, four p one channel swit	N_ = -80V, PRF = 10kHz, pulses, no load,		0.6		mA	
		$V_{EN} = 0 \text{ or } V_{DD}$ (	static)			1	μA	
V <sub>NN</sub> _Supply Current		$V_{EN} = V_{DD}$ , $V_{CLP} = 0$ or $V_{DD}$ , $V_{INN} = V_{INP}$ , f = 5MHz, $V_{PP} = +5V$ , $V_{NN} = -5V$ , no load, one channel switching			9			
	INN_	VEN = VDD, VINC_ = 0 or VDD, VPP_ = +80V, VNN_ = -80V, PRF = 10kHz, f = 10MHz, four pulses, no load, one channel switching			0.6		mA	
LOGIC INPUTS (EN, INN_, INP_	, CLP_)	1		1				
Low-Level Input Voltage	VIL					0.25 x V <sub>DD</sub>	V	
High-Level Input Voltage	Vih			0.75 x V <sub>DD</sub>			V	
Logic-Input Capacitance	CIN				5		рF	
Logic-Input Leakage	lin	$V_{IN} = 0 \text{ or } V_{DD}$			0	±1	μΑ	
OUTPUT (OUT_)		1						
		No load at OUT_		V <sub>NN</sub> _		VPP_	V	
OUT_ Output-Voltage Range	Vout_	100mA load (MAX4940), $V_{CC} = +12V \pm 5\%$		V <sub>NN_</sub> + 1.5		V <sub>PP</sub> 1.5	V	
		100mA load (MA)	100mA load (MAX4940A), $V_{CC} = +12V \pm 5\%$			V <sub>PP</sub> 2.5	V	
Low-Side Output Impedance (MAX4940)	Rols	$I_{OUT_} = -50 \text{mA}$ $V_{CC} = +12V \pm 5\%$ $V_{CC} = +5V \pm 5\%$			7.5 8	14 18	Ω	
High-Side Output Impedance (MAX4940)	ROHS	I <sub>OUT_</sub> = -50mA	$V_{CC} = +12V \pm 5\%$		9	14	Ω	
(IVIAA494U)		_	$V_{CC} = +5V \pm 5\%$		10.5	18		

#### **ELECTRICAL CHARACTERISTICS (continued)**

 $(V_{DD} = +3V, V_{CC} = +12V, V_{EE} = -12V, V_{PP} = +100V, V_{NN} = -100V, T_A = T_{MIN}$  to  $T_{MAX}$ , unless otherwise noted. Typical values are at  $T_A = +25^{\circ}C$ .) (Note 2)

PARAMETER	SYMBOL	CO	NDITIONS	MIN	TYP	MAX	UNITS
Low-Side Output Impedance	Polo	IOUT = -50mA	$V_{CC} = +12V \pm 5\%$		8.5	17	0
(MAX4940A)	Rols	$1001^{-} = -2000$	$V_{CC} = +5V \pm 5\%$		10.0	21	Ω
High-Side Output Impedance	ROHS	IOUT_ = -50mA	$V_{CC} = +12V \pm 5\%$		11.5	17	
(MAX4940A)	NOHS	1001_ = -3011A	$V_{CC} = +5V \pm 5\%$		13.0	21	Ω
Low-Side Signal CLAMP Output	Rolsc	IOUT_ = -50mA	$V_{CC} = +12V \pm 5\%$		18.7	45	Ω
Impedance	HOLSC	1001_ = -3011A	$V_{CC} = +5V \pm 5\%$		20	60	52
High-Side Signal CLAMP Output	Rouco	IOUT_ = -50mA	$V_{CC} = +12V \pm 5\%$		26.5	45	Ω
Impedance	Rohsc	1001_ = -3011A	$V_{CC} = +5V \pm 5\%$		37.0	60	52
PEAK CURRENT							
Low-Side Output Current	IOL	$V_{CC} = +12V \pm 5\%$	, Vout Vnn_ = 100V	1.3	2.0		А
High-Side Output Current	ЮН	$V_{CC} = +12V \pm 5\%$	, V <sub>OUT</sub> V <sub>PP</sub> _ = 100V	1.3	2.0		А
Low-Side Output Current Clamp	IOLC	$V_{CC} = +12V \pm 5\%$	, VOUT_ = +40V	0.47	0.9		^
High-Side Output Current Clamp	Іонс	$V_{CC} = +12V \pm 5\%$	, V <sub>OUT</sub> = +40V	0.47	0.9		A
		MAX4940, MAX49	940A (OUT1_)		75		
Off-Output Capacitance	CO(OFF)	MAX4940A (OUT2	2_)		45		рF
Off-Output Leakage Current	ILK	$V_{NN_{}} = -100V, V_{PI}$ $V_{OUT_{}} = -100V$ to	P_ = +100V, V <sub>EN</sub> = 0, +100V			±1	μA
GATE-SOURCE RESISTANCE				1			I
Gate-Source Resistance	RGS	V <sub>EN</sub> = V <sub>DD</sub>		5	7.5	10	kΩ
DYNAMIC CHARACTERISTICS (			otherwise noted)				I
Logic Input-to-Output Rise Propagation Delay (Figure 1)	tplh	INN_/INP_ at 50%			15		ns
		1					
Logic Input-to-Output Fall Propagation Delay (Figure 1)	t <sub>PHL</sub>	$\frac{\text{INN}_{\text{INP}} \text{ at 50\%}}{\text{V}_{\text{CC}} = +12\text{V}, \text{V}_{\text{PP}}}$	$_{=} +5V, V_{NN} = -5V$		15		ns
Logic Input-to-Output Rise Propagation Delay Clamp (Figure 1)	tplo	INN_/INP_ at 50% VCC = +12V, VPP_	to OUT_ 10/90%, _= +5V, V <sub>NN</sub> _ = -5V		15		ns
Logic Input-to-Output Fall Propagation Delay Clamp (Figure 1)	tрно	INN_/INP_ at 50% V <sub>CC</sub> = +12V, V <sub>PP</sub> _	to OUT_ 10/90%, _= +5V, V <sub>NN</sub> _ = -5V		15		ns
OUT_ Rise Time (GND to V <sub>PP</sub> ) (Figure 1)	trop	V <sub>PP</sub> = +100V, V <sub>NI</sub> V <sub>CC</sub> = +12V ±5%	N_ = -100V, 10% to 90%, %, VEE_ = -VCC_		9	20	ns
OUT_ Rise Time (V <sub>NN_</sub> to V <sub>PP_</sub> ) (Figure 1)	trnp	$V_{PP_} = +100V, V_{NI}$ $V_{CC_} = +12V \pm 5\%$	N_ = -100V, 10% to 90%, %, VEE_ = -VCC_		10.5	35	ns
OUT_ Fall Time (GND to V <sub>NN_</sub> ) (Figure 1)	<sup>t</sup> FON	$V_{PP_} = +100V, V_{NI}$ $V_{CC_} = +12V \pm 5\%$	N_ = -100V, 10% to 90%, %, VEE_ = -VCC_		9	20	ns
OUT_ Fall Time (Vpp_ to V <sub>NN</sub> ) (Figure 1)	tFPN	$V_{PP} = +100V, V_{NI}$ $V_{CC} = +12V \pm 5\%$	N_ = -100V, 10% to 90%, , VEE_ = -VCC_		10.5	35	ns
OUT_ Rise Time (V <sub>NN</sub> to GND) (Figure 1)	<sup>t</sup> RNO	$V_{PP} = +100V, V_{NI}$ $V_{CC} = +12V \pm 5\%$	N_ = -100V, 10% to 90%, , VEE_ = -VCC_		17	35	ns

#### **ELECTRICAL CHARACTERISTICS (continued)**

 $(V_{DD} = +3V, V_{CC} = +12V, V_{EE} = -12V, V_{PP} = +100V, V_{NN} = -100V, T_A = T_{MIN}$  to T\_MAX, unless otherwise noted. Typical values are at T\_A = +25°C.) (Note 2)

PARAMETER SYMBOL CONDITIONS		CONDITIONS	MIN	TYP	MAX	UNITS
OUT_ Fall Time (V <sub>PP</sub> to GND) (Figure 1)	tFPO	$V_{PP}$ = +100V, $V_{NN}$ = -100V, 10% to 90%, $V_{CC}$ = +12V ±5%, $V_{EE}$ = - $V_{CC}$		17	35	ns
Output Enable Time from EN (Figure 2)	t <sub>EN</sub>	VPP_ = +5V, V <sub>NN</sub> _ = -5V			100	ns
Output Disable Time from EN (Figure 2)	tDI	VPP_ = +5V, V <sub>NN</sub> _ = -5V			150	ns
2nd Harmonic Distortion LV	THD2_LV	$f_{OUT} = 5MHz$ , $V_{PP} = -V_{NN} = +5V$ , $V_{CC} = +12V$		-40		dB
2nd Harmonic Distortion HV	THD2_HV	fout_ = 5MHz, Vpp_ = -VNN_ = +50V, VCC = +12V, 10 periods		-45		dB
Pulse Cancellation 2HD		$f_{OUT} = 5MHz$ , $V_{PP} = -V_{NN} = +50V$ , $V_{CC} = +12V$ , 10 periods, 1st harmonic cancellation		-43		dB
RMS Output Jitter	tJ			10		ps
Crosstalk	CT	Adjacent channels, f = 5MHz		-60		dB

 HMS Output Sitter
 LJ
 IO
 ps

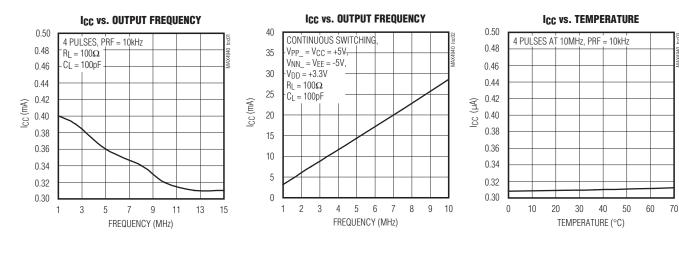
 Crosstalk
 CT
 Adjacent channels, f = 5MHz
 -60
 dB

 Note 2: Specifications are guaranteed for the stated global conditions, unless otherwise noted. 100% production tested at

TA = +70°C. Specifications at TA = 0°C are guaranteed by design.

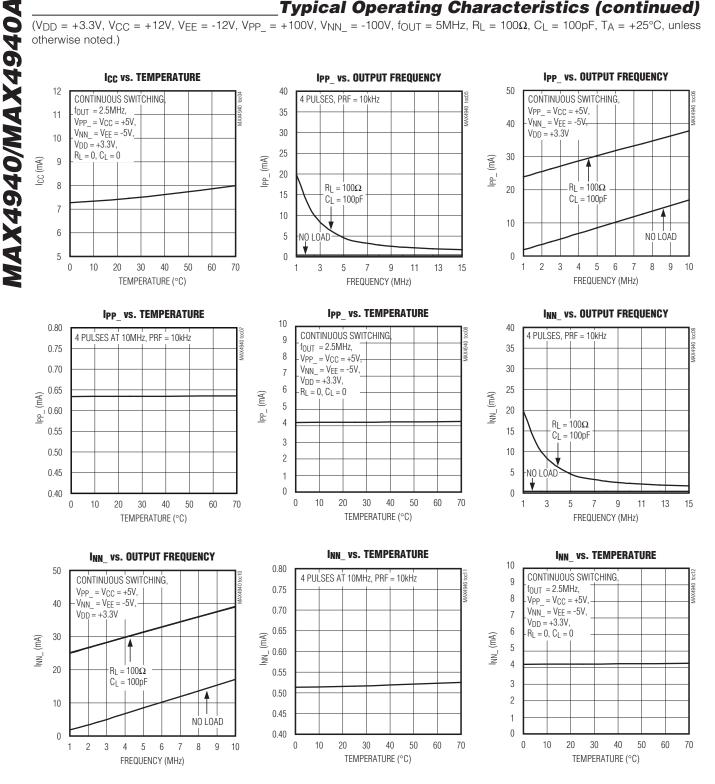
#### **Typical Operating Characteristics**

 $(V_{DD} = +3.3V, V_{CC} = +12V, V_{EE} = -12V, V_{PP} = +100V, V_{NN} = -100V, f_{OUT} = 5MHz, R_L = 100\Omega, C_L = 100pF, T_A = +25^{\circ}C, unless otherwise noted.)$ 



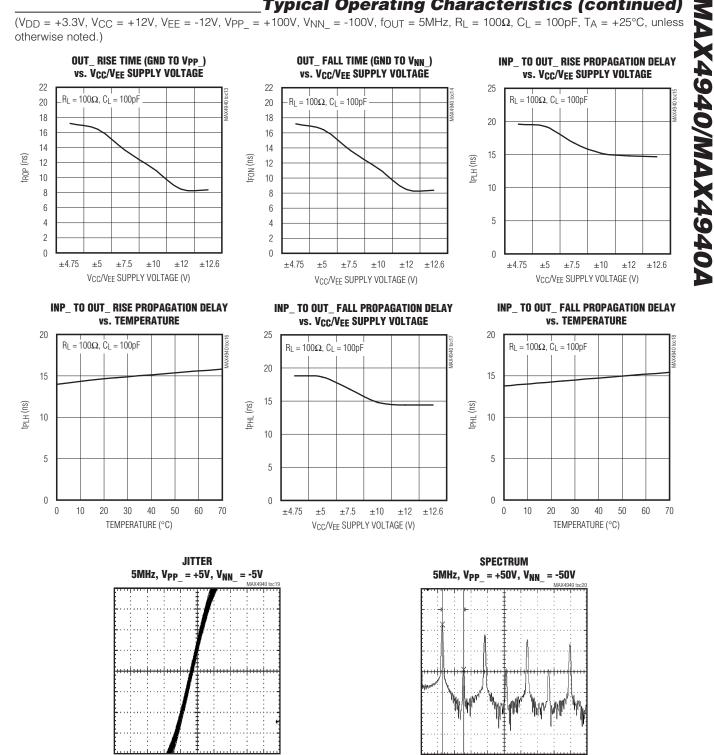


 $(V_{DD} = +3.3V, V_{CC} = +12V, V_{EE} = -12V, V_{PP} = +100V, V_{NN} = -100V, f_{OUT} = 5MHz, R_L = 100\Omega, C_L = 100pF, T_A = +25^{\circ}C, unless = -12V, V_{PP} = +100V, V_{NN} = -100V, f_{OUT} = 5MHz, R_L = 100\Omega$ otherwise noted.)



#### **Typical Operating Characteristics (continued)**

 $(V_{DD} = +3.3V, V_{CC} = +12V, V_{EE} = -12V, V_{PP} = +100V, V_{NN} = -100V, f_{OUT} = 5MHz, R_L = 100\Omega, C_L = 100pF, T_A = +25^{\circ}C, unless = -12V, V_{PP} = +100V, V_{NN} = -100V, f_{OUT} = 5MHz, R_L = 100\Omega, C_L = 100pF, T_A = +25^{\circ}C, unless = -12V, V_{PP} = +100V, V_{NN} = -100V, f_{OUT} = 5MHz, R_L = 100\Omega, C_L = 100pF, T_A = +25^{\circ}C, unless = -12V, V_{PP} = +100V, V_{PP} = -100V, f_{OUT} = -100PF, T_A = +25^{\circ}C, unless = -100V, f_{OUT} = -100V, f_{OU$ otherwise noted.)



MIXIM

#### **Pin Description**

PIN	NAME	FUNCTION
1	INP1A	Channel 1A High-Side Logic Input. See the Truth Tables section.
2	CLP1A	Channel 1A Clamp Logic Input. Clamp is turned on when CLP1A is high and when INP1A and INN1A are low. See the <i>Truth Table</i> section.
3	INN1A	Channel 1A Low-Side Logic Input. See the Truth Tables section.
4	INP2A	Channel 2A High-Side Logic Input. See the Truth Tables section.
5	CLP2A	Channel 2A Clamp Logic Input. Clamp is turned on when CLP2A is high and when INP2A and INN2A are low. See the <i>Truth Tables</i> section.
6	INN2A	Channel 2A Low-Side Logic Input. See the Truth Tables section.
7	AGND	Analog Ground. Must be connected to common GND.
8	EN	Enable Logic Input. Drive EN high to enable OUT1A, OUT1B, OUT2A, and OUT2B.
9	INP2B	Channel 2B High-Side Logic Input. See the Truth Tables section.
10	CLP2B	Channel 2B Clamp Logic Input. Clamp is turned on when CLP2B is high and when INP2B and INN2B are low. See the <i>Truth Tables</i> section.
11	INN2B	Channel 2B Low-Side Logic Input. See the Truth Tables section.
12	INP1B	Channel 1B High-Side Logic Input. See the Truth Tables section.
13	CLP1B	Channel 1B Clamp Logic Input. Clamp is turned on when CLP1B is high and when INP1B and INN1B are low. See the <i>Truth Tables</i> section.
14	INN1B	Channel 1B Low-Side Logic Input. See the Truth Tables section.
15	VEE	Negative Supply Input. Gate-drive supply voltage for the clamp. Bypass VEE to GND with a $0.1\mu$ F capacitor as close as possible to the device.
16, 27, 29, 34, 37, 42, 44, 55	GND	Ground
17, 54	Vcc	Gate-Drive Supply Voltage Input. Bypass V <sub>CC</sub> to GND with a 0.1µF capacitor as close as possible to the device.
18	C <sub>DP1B</sub>	Channel 1B High-Side Driver Output. Connect a 3.3nF capacitor between CDP1B and CGP1B as close as possible to the device.
19	C <sub>DN1B</sub>	Channel 1B Low-Side Driver Output. Connect a 3.3nF capacitor between $C_{DN1B}$ and $C_{GN1B}$ as close as possible to the device.
20	C <sub>DN2B</sub>	Channel 2B Low-Side Driver Output. Connect a 3.3nF capacitor between $C_{DN2B}$ and $C_{GN2B}$ as close as possible to the device.
21	C <sub>DP2B</sub>	Channel 2B High-Side Driver Output. Connect a 3.3nF capacitor between CDP2B and CGP2B as close as possible to the device.
22	C <sub>GP2B</sub>	Channel 2B High-Side Gate Input. Connect a 3.3nF capacitor between CDP2B and CGP2B as close as possible to the device.
23	C <sub>GN2B</sub>	Channel 2B Low-Side Gate Input. Connect a 3.3nF capacitor between CDN2B and CGN2B as close as possible to the device.
24	C <sub>GN1B</sub>	Channel 1B Low-Side Gate Input. Connect a 3.3nF capacitor between CDN1B and CGN1B as close as possible to the device.
25	C <sub>GP1B</sub>	Channel 1B High-Side Gate Input. Connect a 3.3nF capacitor between CDP1B and CGP1B as close as possible to the device.

### Pin Description (continued)

PIN	NAME	FUNCTION
26, 45	VPP1	Channel 1A, 1B High-Side Positive Supply Voltage Input. Bypass $V_{PP1}$ to GND with a 0.1 $\mu$ F capacitor as close as possible to the device.
28	OUT1B	Channel 1B Output
30, 41	V <sub>NN1</sub>	Channel 1A, 1B Low-Side Negative Supply Voltage Input. Bypass $V_{NN1}$ to GND with a 0.1 $\mu$ F capacitor as close as possible to the device.
31, 40	V <sub>NN2</sub>	Channel 2A, 2B Low-Side Negative Supply Voltage Input. Bypass $V_{NN2}$ to GND with a 0.1 $\mu$ F capacitor as close as possible to the device.
32, 39	N.C.	No Connection. Not connected internally.
33	OUT2B	Channel 2B Output
35, 36	VPP2	Channel 2A, 2B High-Side Positive Supply Voltage Input. Bypass $V_{PP2}$ to GND with a 0.1 $\mu$ F capacitor as close as possible to the device.
38	OUT2A	Channel 2A Output
43	OUT1A	Channel 1A Output
46	C <sub>GP1A</sub>	Channel 1A High-Side Gate Input. Connect a 3.3nF capacitor between CDP1A and CGP1A as close as possible to the device.
47	CGN1A	Channel 1A Low-Side Gate Input. Connect a 3.3nF capacitor between $C_{DN1A}$ and $C_{GN1A}$ as close as possible to the device.
48	CGN2A	Channel 2A Low-Side Gate Input. Connect a 3.3nF capacitor between C <sub>DN2A</sub> and C <sub>GN2A</sub> as close as possible to the device.
49	CGP2A	Channel 2A High-Side Gate Input. Connect a 3.3nF capacitor between CDP2A and CGP2A as close as possible to the device.
50	CDP2A	Channel 2A High-Side Driver Output. Connect a 3.3nF capacitor between CDP2A and CGP2A as close as possible to the device.
51	CDN2A	$\label{eq:Channel 2A Low-Side Driver Output. Connect a 3.3nF capacitor between C_{DN2A} and C_{GN2A} as close as possible to the device.$
52	C <sub>DN1A</sub>	$\label{eq:Channel 1A Low-Side Driver Output. Connect a 3.3nF capacitor between C_{DN1A} and C_{GN1A} as close as possible to the device.$
53	C <sub>DP1A</sub>	Channel 1A High-Side Driver Output. Connect a 3.3nF capacitor between CDP1A and CGP1A as close as possible to the device.
56	VDD	Logic-Supply Voltage Input. Bypass $V_{DD}$ to GND with a 0.1 $\mu$ F capacitor as close as possible to the device.
_	EP	Exposed Pad. EP must be connected to VNN1.

#### **Detailed Description**

The MAX4940/MAX4940A are quad high-voltage, highspeed pulsers that can be independently configured for either unipolar/bipolar/multilevel pulse outputs (see Figures 5 and 6.). These devices have independent logic inputs for full pulse control and independent active clamps. The clamp input, CLP\_, can be set high to activate the clamp automatically when the device is not pulsing to the positive or negative high-voltage supplies.

#### Logic Inputs (INP\_, INN\_, CLP\_, EN)

INP\_ controls the on and off states of the high-side FET, INN\_ controls the on and off states of the low-side FET, and CLP\_ controls the active clamp. A global enable input (EN) can be used to enable/disable all channels. These signals give complete control of the output stage of each driver (see the *Truth Tables* section for all logic combinations). The MAX4940/MAX4940A logic inputs are **CMOS logic compatible and the logic levels are ref**erenced to V<sub>DD</sub> for maximum flexibility. The low 5pF (typ) input capacitance of the logic inputs reduce loading and increase switching speed.

#### **Truth Tables**

#### MAX4940

	INP	UTS		OUTPUTS			
EN	INP_	INN_	CLP_	OUT_	STATE		
0	Х	Х	Х	High impedance	Powered up, INP_/INN_ disabled.		
1	0	0	0	High impedance	Powered up, all inputs enabled.		
1	0	0	1	GND	Powered up, all inputs enabled.		
1	0	1	Х	VNN_	Powered up, all inputs enabled.		
1	1	0	Х	VPP_	Powered up, all inputs enabled.		
1	1	1	Х	Not allowed	Not allowed.		

#### **MAX4940A**

	INPUTS		OUTPUTS		
EN	INP1A INP1B	INN1A INN1B	CLP1A CLP1B	OUT1A OUT1B	STATE
0	Х	Х	Х	High impedance	Powered up, INP_/INN_ disabled.
1	0	0	0	High impedance	Powered up, all inputs enabled.
1	0	0	1	GND	Powered up, all inputs enabled.
1	0	1	0	V <sub>NN</sub> _	Powered up, all inputs enabled.
1	1	0	0	VPP_	Powered up, all inputs enabled.
1	1	1	1	Not allowed	Not allowed.

	INP	UTS		OUTPUTS	
EN	INP2A INP2B	INN2A INN2B	CLP2A CLP2B	OUT2A OUT2B	STATE
0	Х	Х	Х	High impedance	Powered up, INP_/INN_ disabled.
1	0	0	0	High impedance	Powered up, all inputs enabled.
1	0	0	1	GND	Powered up, all inputs enabled.
1	0	1	Х	VNN_	Powered up, all inputs enabled.
1	1	0	Х	V <sub>PP</sub> _	Powered up, all inputs enabled.
1	1	1	Х	Not allowed	Not allowed.

X = Don't care.

0 = Logic-low.

1 = Logic-high.

#### **Active Clamps**

The MAX4940/MAX4940A feature an integrated active clamp circuit to improve pulse quality and reduce 2nd harmonic distortion. The clamp circuit consists of an n-channel (DC-coupled) and a p-channel (DC-coupled) high-voltage FETs that are switched on or off by the logic clamp input (CLP\_).

The MAX4940/MAX4940A feature protected clamp devices, allowing the clamp circuit to be used in bipolar pulsing circuits (see Figures 3 and 4). A diode in series with the OUT\_ output prevents the body diode of the low-side FET from turning on when a voltage lower than GND is present. Another diode in series with the OUT\_ output prevents the body diode of the high-side FET from turning on when a voltage higher than ground is present. The MAX4940/MAX4940A have an active clamp on all outputs.

For the MAX4940 only, the user can connect the active clamp input (CLP\_) to a logic-high voltage and drive only the INP\_ and INN\_ inputs to minimize the number of signals used to drive the device. In this case, whenever both the INP\_ and INN\_ inputs are low and the CLP\_ input is high, the active clamp circuit pulls the output to GND (see the *Truth Tables* section for more information).

#### Integrated Blocking Diodes (MAX4940A Only)

The high-voltage OUT2A/OUT2B outputs of the MAX4940A feature integrated blocking diodes that allow the user to implement multilevel pulsing by connecting the outputs of multiple pulser channels in parallel. Internal diodes in series with the OUT2A and OUT2B outputs prevent the body diode of the high-side and low-side FETs from switching on when a voltage greater than VNN2 or VPP2 is present on the output (see Figure 4).

#### **Thermal Protection**

A thermal shutdown circuit with a typical threshold of +155°C prevents damage due to excessive **power dis**sipation. When the junction temperature exceeds  $T_J$  = +155°C, all outputs are disabled. Normal operation typically resumes after the IC's junction temperature drops below +130°C.

#### \_Applications Information

#### **AC-Coupling Capacitor Selection**

The value of all AC-coupling capacitors (between C<sub>DP</sub> and C<sub>GP</sub>, and between C<sub>DN</sub> and C<sub>GN</sub>) should be between 1nF to 10nF. The voltage rating of the capacitor should be greater than V<sub>PP</sub> and V<sub>NN</sub>. The capacitors should be placed as close as possible to the device.

#### **Power Dissipation**

MAX4940/MAX4940A

The power dissipation of the MAX4940/MAX4940A consists of three major components caused by the current consumption from V<sub>CC</sub>, V<sub>PP</sub>, and V<sub>NN</sub>. The sum of these components (P<sub>VCC</sub>, P<sub>VPP</sub>, and P<sub>VNN</sub>) must be kept below the maximum power-dissipation limit. See the *Typical Operating Characteristics* section for more information on typical supply currents versus switching frequencies.

The device consumes most of the supply current from VCC supply to charge and discharge internal nodes such as the gate capacitance of the high-side FET (C<sub>P</sub>) and the low-side FET (C<sub>N</sub>). Neglecting the small quiescent supply current and a small amount of current used to charge and discharge the capacitances at the internal gate clamp FETs, the power consumption can be estimated as follows:

$$P_{VCC} = \left[ \left( C_N \times V_{CC}^2 \times f_{IN} \right) + \left( C_P \times V_{CC}^2 \times f_{IN} \right) \right] \times (BRF \times BTD)$$
$$f_{IN} = f_{INN} + f_{INP}$$

where fINN\_ and fINP\_ are the switching frequency of the inputs INN\_, INP\_, respectively, and where BRF is the burst response frequency, and BTD is the burst time duration. The typical values of the gate capacitances are  $C_N = 1.2\mu$ F,  $C_P = 0.4\mu$ F.

See the Typical Operating Characteristics for VPP\_ and VNN\_ power consumption.

#### **Power Supplies and Bypassing**

The MAX4940/MAX4940A operate from independent supply voltage sets (only V<sub>DD</sub>, V<sub>CC</sub>, and V<sub>EE</sub> are common to all channels). V<sub>PP1</sub>/V<sub>NN1</sub> supply two channels and V<sub>PP2</sub>/V<sub>NN2</sub> supply the other two channels. The logic input circuit operates from a +2.37V to +6V single supply (V<sub>DD</sub>). The level-shift driver dual supplies, V<sub>CC</sub>/V<sub>EE</sub> operate from  $\pm 4.75V$  to  $\pm 12.6V$ .

The VPP\_/VNN\_ high-side and low-side supplies are driven from a single positive supply up to +220V, from a single negative supply up to -220V, or from  $\pm$ 110V dual supplies. Either VPP\_ or VNN\_ can be set at 0. Bypass each supply input to ground with a 0.1µF capacitor as close as possible to the device.

Depending on the applications, additional bypassing may be needed to maintain the input of both V<sub>NN</sub> and V<sub>PP</sub> stable during output transitions. For example, with C<sub>OUT</sub> = 100pF and R<sub>OUT</sub> = 100 $\Omega$  load, the use of an additional 10µF (typ) electrolytic capacitor is recommended.



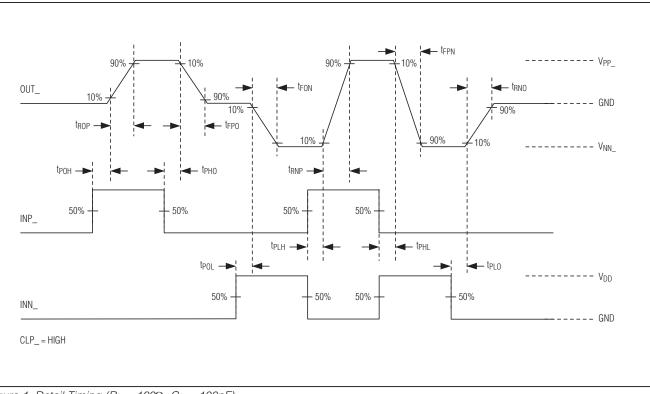
#### **Exposed Pad and Layout Concerns**

The MAX4940/MAX4940A provide an exposed pad (EP) underneath the TQFN package for improved thermal performance. EP is internally connected to  $V_{NN1}$ . Connect EP to  $V_{NN1}$  externally. To aid heat dissipation, connect EP to a similarly sized pad on the component side of the PCB. This pad should be connected through the solder-side copper by several plated holes to a large heat spreading copper area to conduct heat away from the device.

The MAX4940/MAX4940A high-speed pulsers require lowinductance bypass capacitors to their supply inputs. Highspeed PCB trace design practices are recommended. Pay particular attention to minimize trace lengths and use sufficient trace width to reduce inductance. Use of surfacemount components is recommended.

#### **Supply Sequencing**

In a typical trilevel application when V<sub>NN1</sub> and V<sub>NN2</sub> are externally shorted (V<sub>NN1</sub> = V<sub>NN2</sub>), the MAX4940/ MAX4940A do not require any power sequencing. In general, and in particular for the multilevel application, V<sub>NN1</sub> must be less than or equal to V<sub>NN2</sub> (V<sub>NN1</sub>  $\leq$  V<sub>NN2</sub>) at all times. No other power-supply sequencing is required for the MAX4940/MAX4940A.



#### **Timing Diagrams**

Figure 1. Detail Timing ( $R_L = 100\Omega$ ,  $C_L = 100pF$ )

### Timing Diagrams (continued)

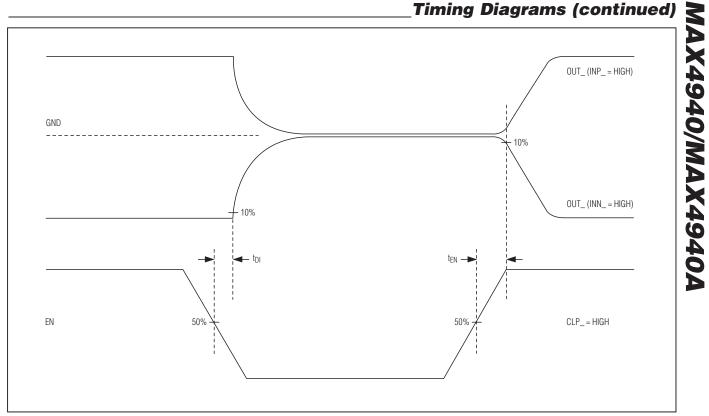


Figure 2. Enable Timing ( $R_L = 100\Omega$ ,  $C_L = 100pF$ )

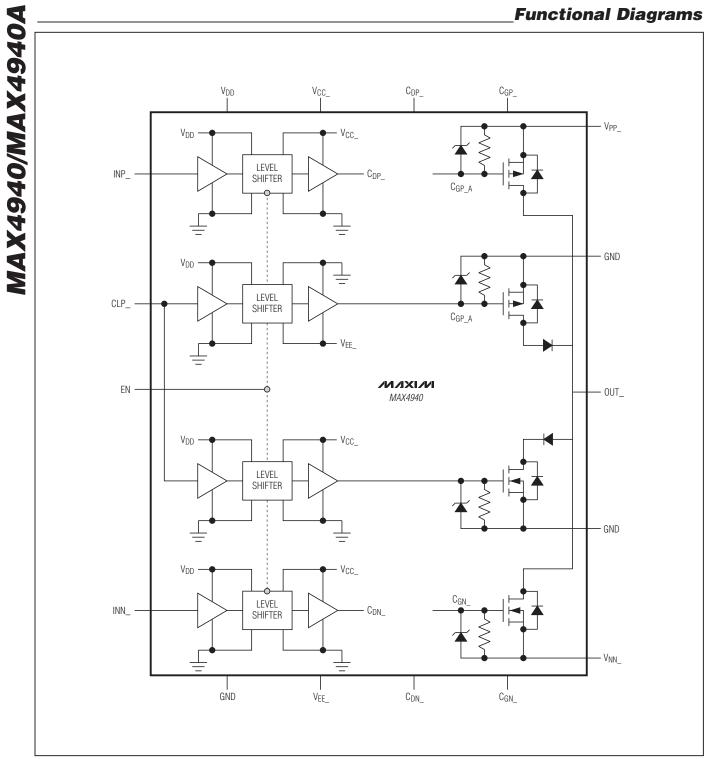


Figure 3. MAX4940 Simplified Functional Diagram for One Channel

### Functional Diagrams (continued)

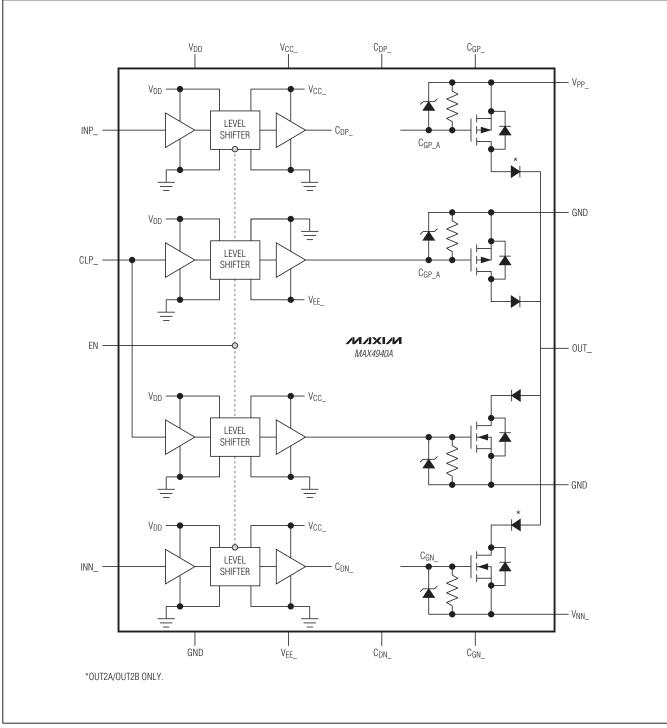


Figure 4. MAX4940A Simplified Functional Diagram for One Channel

**MAX4940/MAX4940A** 

**Typical Application Circuits** 

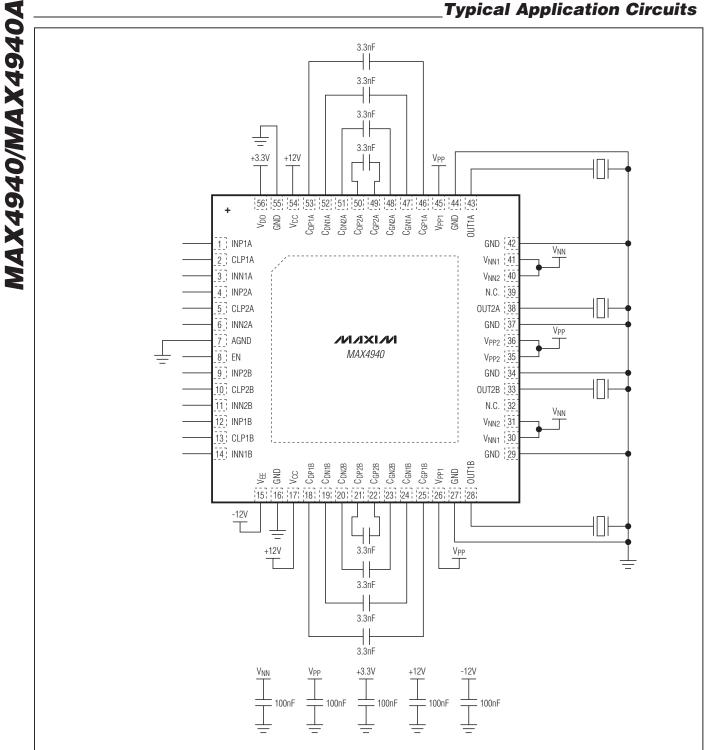


Figure 5. MAX4940 Quad Pulsing with Always-On Active Return-to-Zero

#### **Typical Application Circuits (continued)**

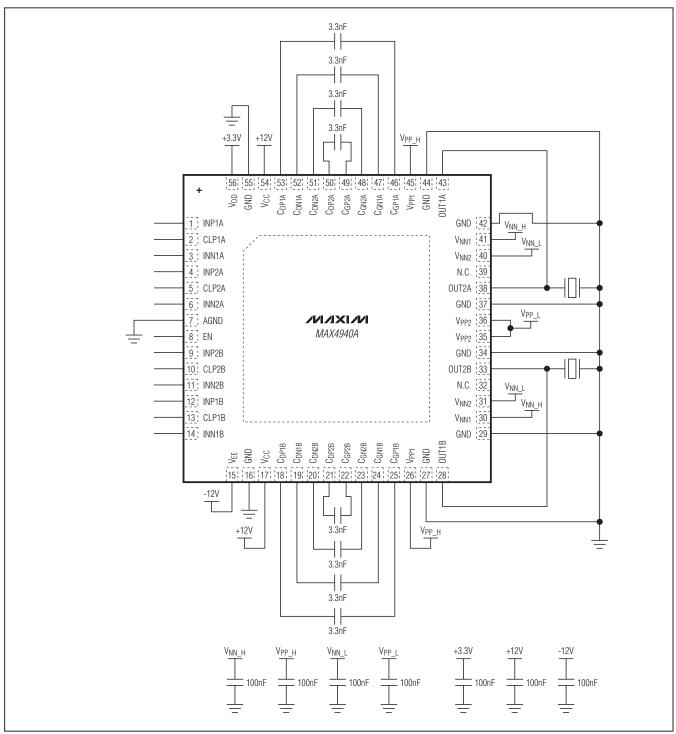


Figure 6. MAX4940A Dual Five-Level Pulsing

MAX4940/MAX4940A

Chip Information

#### Package Information

PROCESS: BiCMOS

For the latest package outline information and land patterns, go to **www.maxim-ic.com/packages**.

PACKAGE TYPE	PACKAGE CODE	DOCUMENT NO.
56 TQFN	T5688-3	<u>21-0135</u>

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